**AMENDMENT TO THE CLAIMS**

Please amend the claims as follows:

1. (Canceled)

2. (New) A method for forming an insulating ceramic film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and

forming the insulating ceramic film on a surface of an object in said reaction chamber,

wherein a power value of said pulsed electromagnetic wave is higher than a power value of said continuous electromagnetic wave.

3. (New) A method according to claim 2 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

4. (New) A method for forming an insulating ceramic film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed microwave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed microwave; and

forming the insulating ceramic film on a surface of an object in the reaction chamber using the plasma,

wherein a power value of said pulsed microwave is higher than a power value of said continuous electromagnetic wave,

5. (New) A method according to claim 4 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

6. (New) A method for forming an insulating ceramic film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and

forming the insulating ceramic film on a surface of an object in said reaction chamber,

wherein a power value of said pulsed electromagnetic wave is higher than a power value of said continuous electromagnetic wave, and

wherein a frequency of said pulsed electromagnetic wave is the same as a frequency of said continuous electromagnetic wave.

7. (New) A method according to claim 6 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

8. (New) A method for forming an insulating ceramic film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and

forming the insulating ceramic film on a surface of an object in said reaction chamber,

wherein a frequency of said pulsed electromagnetic wave is different from a frequency of said continuous electromagnetic wave.

9. (New) A method according to claim 8 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

10. (New) A method for forming a metallic film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and

forming the metallic film on a surface of an object in said reaction chamber,

wherein a power value of said pulsed electromagnetic wave is higher than a power value of said continuous electromagnetic wave.

11. (New) A method according to claim 10 wherein said metallic film comprises a material selected from the group consisting of tungsten, titanium, molybdenum and a silicide thereof.

12. (New) A method according to claim 10 further comprising a step of

applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

13. (New) A method for forming a metallic film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed microwave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed microwave; and

forming the metallic film on a surface of an object in the reaction chamber using the plasma,

wherein a power value of said pulsed microwave is higher than a power value of said continuous electromagnetic wave.

14. (New) A method according to claim 13 wherein said metallic film comprises a material selected from the group consisting of tungsten, titanium, molybdenum and a silicide thereof.

15. (New) A method according to claim 13 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

16. (New) A method for forming a metallic film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and

forming the metallic film on a surface of an object in said reaction chamber,

wherein a power value of said pulsed electromagnetic wave is higher than a power value of said continuous electromagnetic wave, and

wherein a frequency of said pulsed electromagnetic wave is the same as a frequency of said continuous electromagnetic wave.

17. (New) A method according to claim 18 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

18. (New) A method for forming a metallic film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and

forming the metallic film on a surface of an object in said reaction chamber,

wherein a frequency of said pulsed electromagnetic wave is different from a frequency of said continuous electromagnetic wave.

19. (New) A method according to claim 18 wherein said metallic film comprises a material selected from the group consisting of tungsten, titanium, molybdenum and a silicide thereof.

20. (New) A method according to claim 18 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.